



**THE DATASHEET OF  
IRFR3706CPBF**



**SMPS MOSFET**

**IRFR3706CPbF**  
**IRFU3706CPbF**

**Applications**

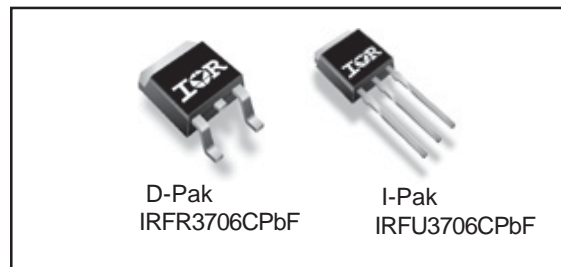
- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use
- High Frequency Buck Converters for Computer Processor Power
- Lead-Free

HEXFET® Power MOSFET

<b>V<sub>DSS</sub></b>	<b>R<sub>DS(on)</sub> max</b>	<b>I<sub>D</sub></b>
<b>20V</b>	<b>9.0mΩ</b>	<b>75A<sup>④</sup></b>

**Benefits**

- Ultra-Low Gate Impedance
- Very Low RDS(on) at 4.5V V<sub>GS</sub>
- Fully Characterized Avalanche Voltage and Current



**Absolute Maximum Ratings**

Symbol	Parameter	Max.	Units
V <sub>DS</sub>	Drain-Source Voltage	20	V
V <sub>GS</sub>	Gate-to-Source Voltage	± 12	V
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	75 <sup>④</sup>	A
I <sub>D</sub> @ T <sub>C</sub> = 100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	53 <sup>④</sup>	
I <sub>DM</sub>	Pulsed Drain Current <sup>①</sup>	280	
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Maximum Power Dissipation <sup>③</sup>	88	W
P <sub>D</sub> @ T <sub>C</sub> = 100°C	Maximum Power Dissipation <sup>③</sup>	44	W
	Linear Derating Factor	0.59	mW/°C
T <sub>J</sub> , T <sub>STG</sub>	Junction and Storage Temperature Range	-55 to + 175	°C

**Thermal Resistance**

	Parameter	Typ.	Max.	Units
R <sub>θJC</sub>	Junction-to-Case <sup>⑤</sup>	—	1.7	°C/W
R <sub>θJA</sub>	Junction-to-Ambient (PCB mount)* <sup>⑤</sup>	—	50	
R <sub>θJA</sub>	Junction-to-Ambient <sup>⑤</sup>	—	110	

\* When mounted on 1" square PCB (FR-4 or G-10 Material) .  
 For recommended footprint and soldering techniques refer to application note #AN-994

Notes ① through ⑤ are on page 10

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# IRFR/U3706CPbF

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## Static @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.021	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	6.9	9.0	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 15A ③
		—	8.1	11		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 12A ③
		—	11.5	23		V <sub>GS</sub> = 2.8V, I <sub>D</sub> = 7.5A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	0.6	—	2.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	20	μA	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V
		—	—	100		V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	200	nA	V <sub>GS</sub> = 12V
	Gate-to-Source Reverse Leakage	—	—	-200		V <sub>GS</sub> = -12V

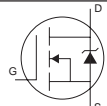
## Dynamic @ T<sub>J</sub> = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g <sub>fs</sub>	Forward Transconductance	53	—	—	S	V <sub>DS</sub> = 16V, I <sub>D</sub> = 57A
Q <sub>g</sub>	Total Gate Charge	—	23	35	nC	I <sub>D</sub> = 28A V <sub>DS</sub> = 10V V <sub>GS</sub> = 4.5V ③ V <sub>GS</sub> = 0V, V <sub>DS</sub> = 10V
Q <sub>gs</sub>	Gate-to-Source Charge	—	8.0	12		
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	5.5	8.3		
Q <sub>oss</sub>	Output Gate Charge	—	16	24		
R <sub>g</sub>	Gate Resistance	—	1.8	—		
t <sub>d(on)</sub>	Turn-On Delay Time	—	6.8	—	ns	V <sub>DD</sub> = 10V I <sub>D</sub> = 28A R <sub>G</sub> = 1.8Ω V <sub>GS</sub> = 4.5V ③
t <sub>r</sub>	Rise Time	—	87	—		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	17	—		
t <sub>f</sub>	Fall Time	—	4.8	—		
C <sub>iss</sub>	Input Capacitance	—	2410	—	pF	V <sub>GS</sub> = 0V V <sub>DS</sub> = 10V f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	1070	—		
C <sub>rss</sub>	Reverse Transfer Capacitance	—	140	—		

## Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy②	—	220	mJ
I <sub>AR</sub>	Avalanche Current①	—	28	A

## Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	75④	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	280		
V <sub>SD</sub>	Diode Forward Voltage	—	0.88	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 36A, V <sub>GS</sub> = 0V ③
		—	0.82	—		T <sub>J</sub> = 125°C, I <sub>S</sub> = 36A, V <sub>GS</sub> = 0V ③
t <sub>rr</sub>	Reverse Recovery Time	—	45	68	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 36A, V <sub>R</sub> = 20V
Q <sub>rr</sub>	Reverse Recovery Charge	—	65	98	nC	di/dt = 100A/μs ③
t <sub>rr</sub>	Reverse Recovery Time	—	49	74	ns	T <sub>J</sub> = 125°C, I <sub>F</sub> = 36A, V <sub>R</sub> = 20V
Q <sub>rr</sub>	Reverse Recovery Charge	—	78	120	nC	di/dt = 100A/μs ③

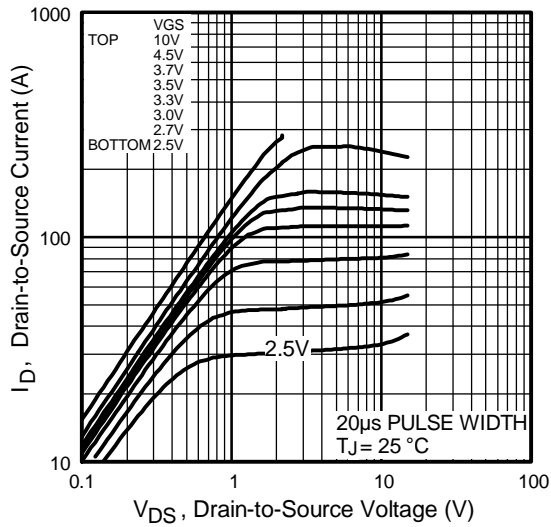


Fig 1. Typical Output Characteristics

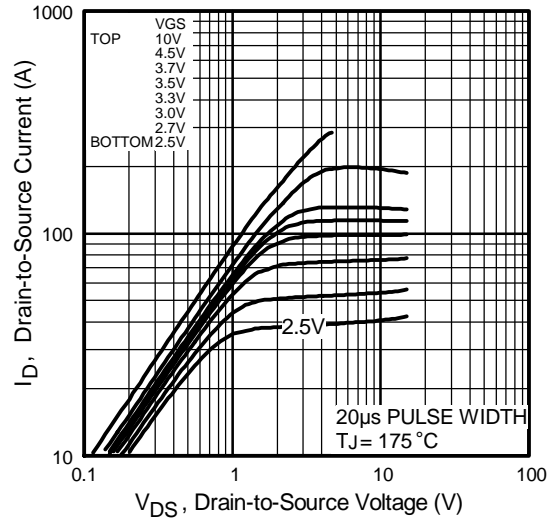


Fig 2. Typical Output Characteristics

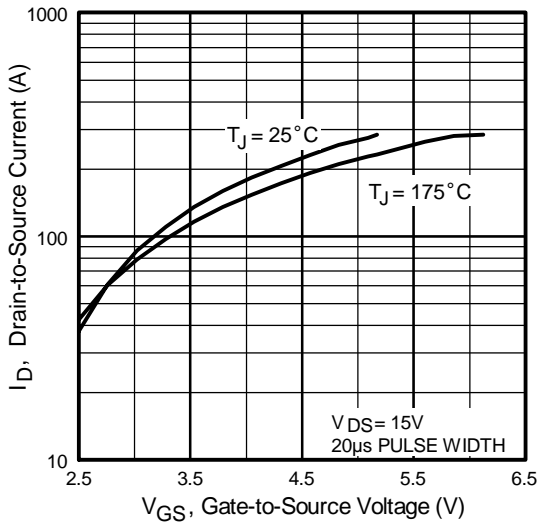


Fig 3. Typical Transfer Characteristics

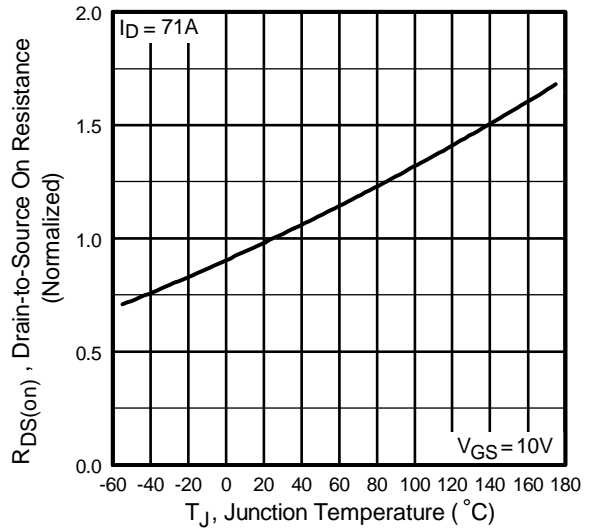
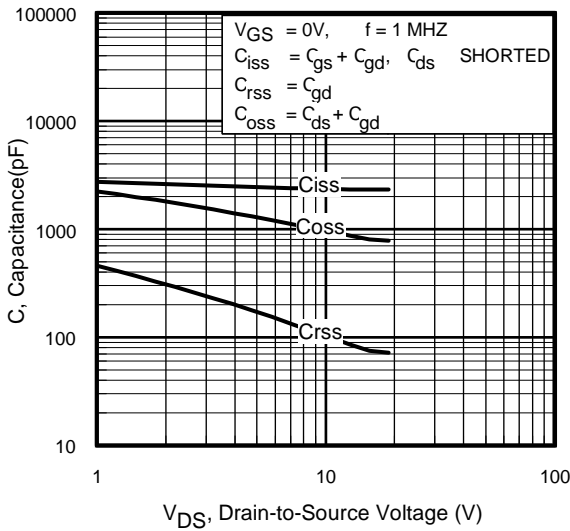
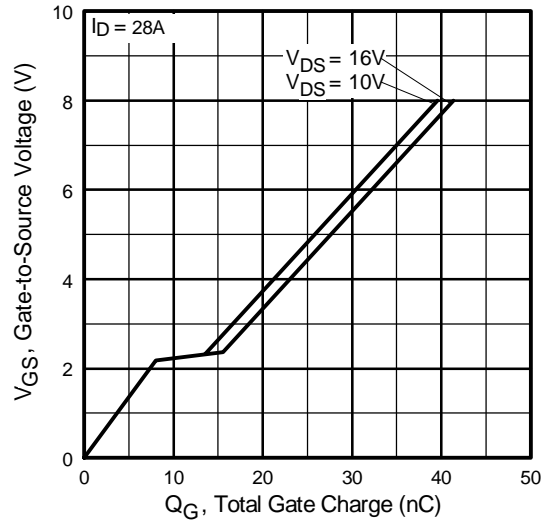


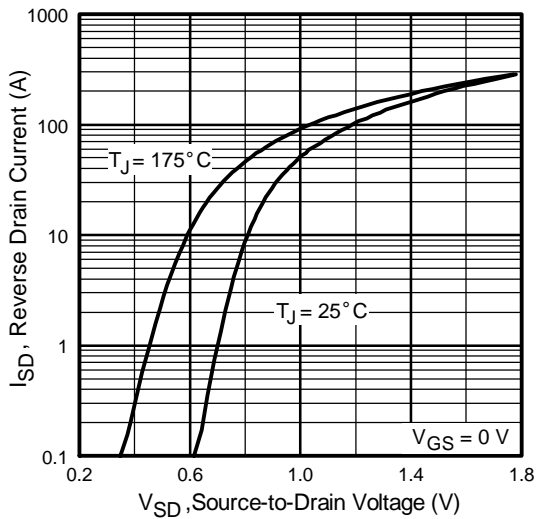
Fig 4. Normalized On-Resistance Vs. Temperature



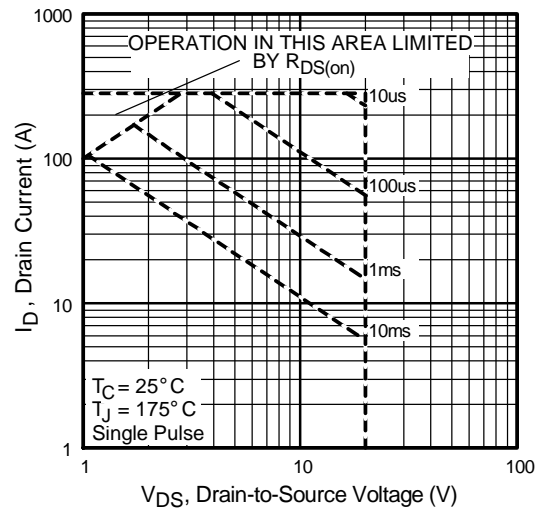
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



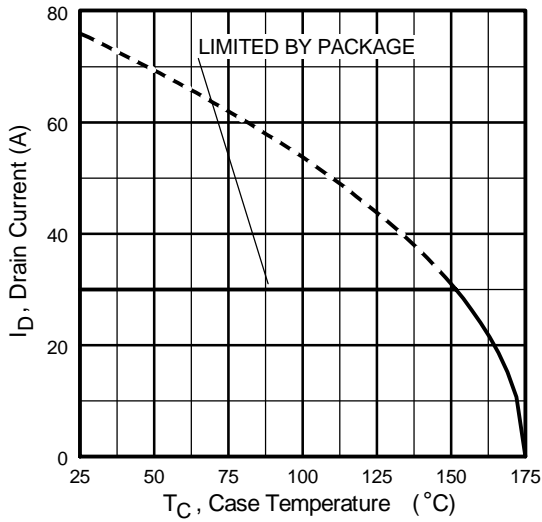
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



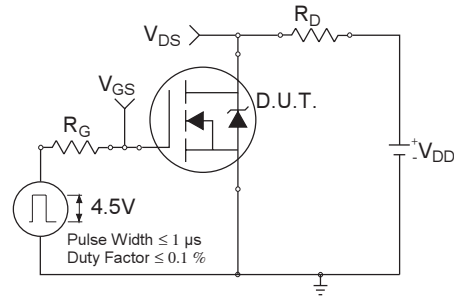
**Fig 7.** Typical Source-Drain Diode Forward Voltage



**Fig 8.** Maximum Safe Operating Area



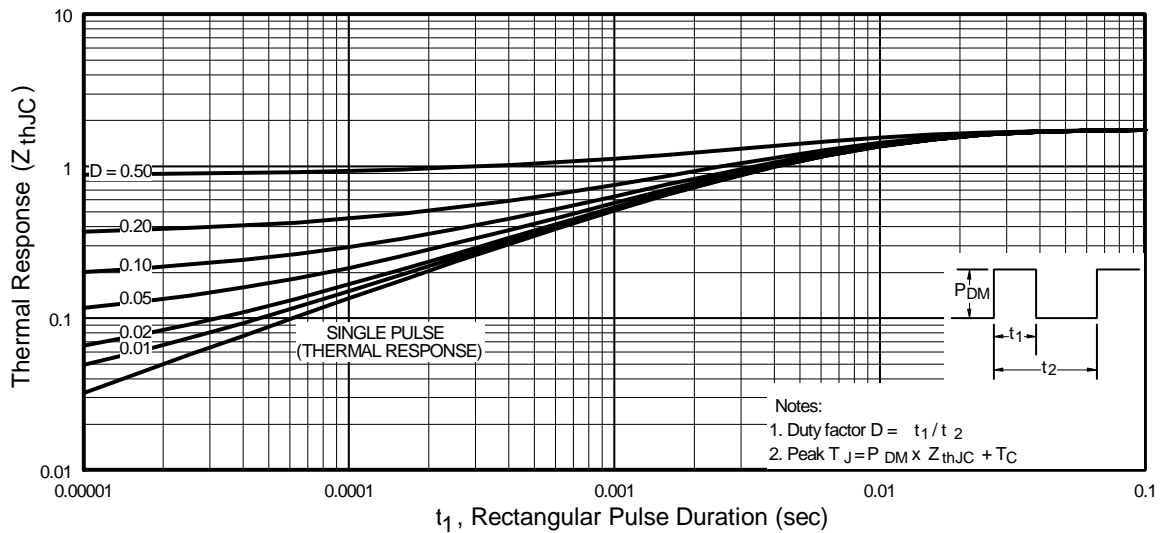
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit



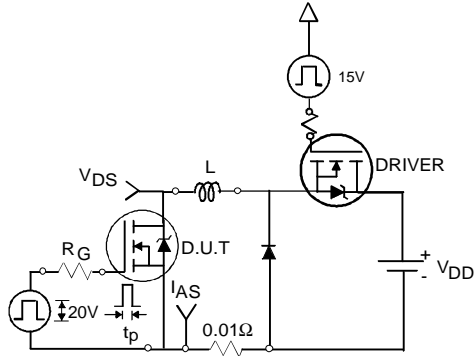
**Fig 10b.** Switching Time Waveforms



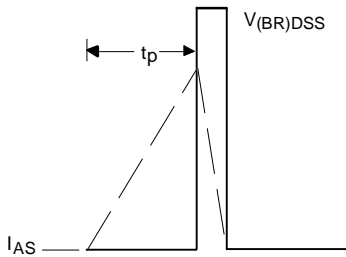
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

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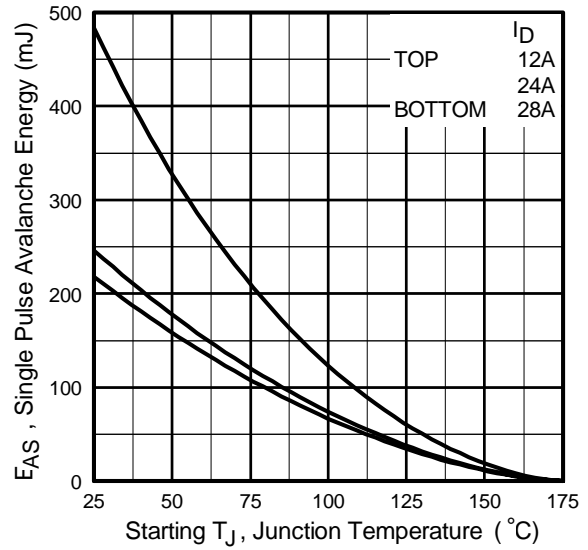
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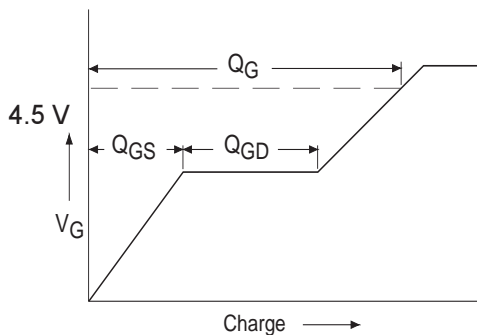
**Fig 12a.** Unclamped Inductive Test Circuit



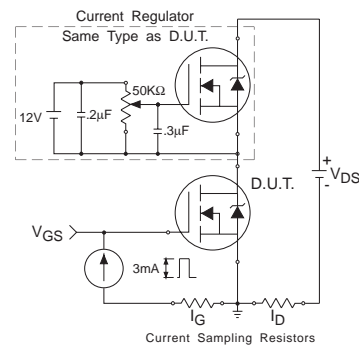
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current

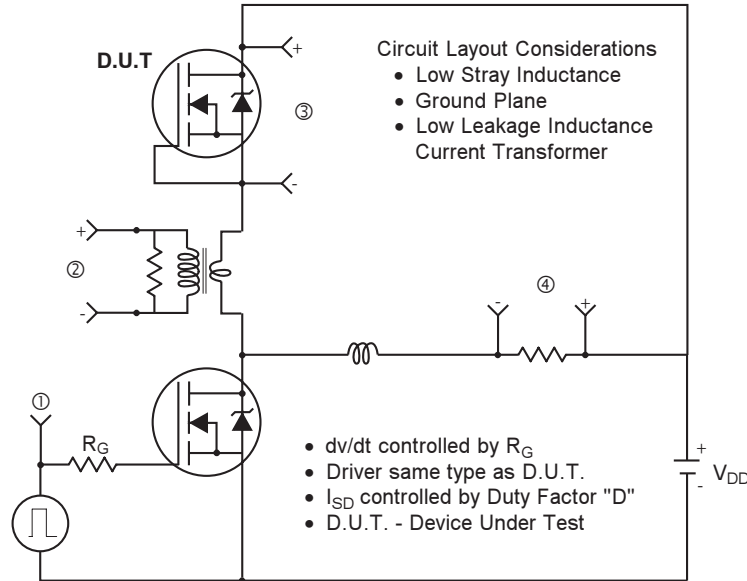


**Fig 13a.** Basic Gate Charge Waveform



**Fig 13b.** Gate Charge Test Circuit

**Peak Diode Recovery dv/dt Test Circuit**



\*  $V_{GS} = 5V$  for Logic Level Devices

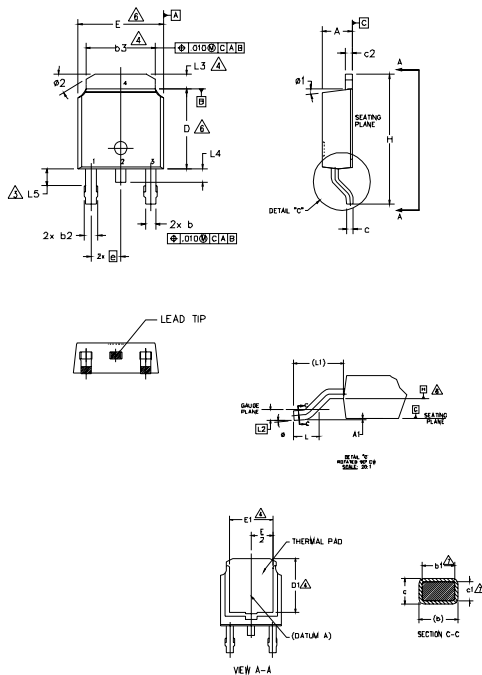
**Fig 14.** For N-Channel HEXFET® Power MOSFETs

# IRFR/U3706CPbF

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## D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



**NOTES:**

- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
- 3.- LEAD DIMENSION UNCONTROLLED IN L5.
- 4.- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
- 5.- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
- 6.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
- 7.- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
- 8.- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
- 9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	-	0.13	-	.005	
b	0.84	0.89	.025	.035	
b1	0.65	0.79	.025	.031	7
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	7
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	6
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	6
E1	4.32	-	.170	-	4
e	2.29 BSC		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 BSC		.108 REF.		
L2	0.51 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	4
L4	-	1.02	-	.040	
L5	1.14	1.52	.045	.060	3
ø1	0"	10"	0"	10"	
ø2	25"	35"	25"	35"	

**LEAD ASSIGNMENTS**

**HEXFET**

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

**IGBT & CoPAK**

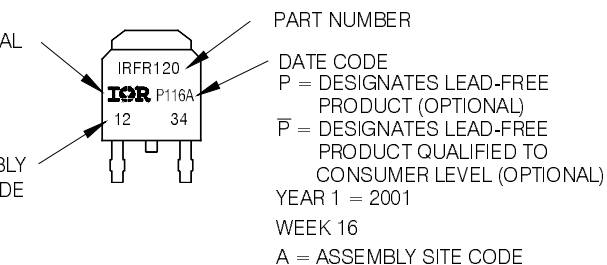
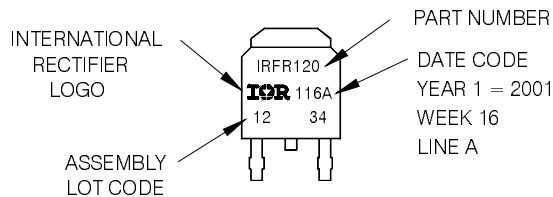
- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

## D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120  
WITH ASSEMBLY  
LOT CODE 1234  
ASSEMBLED ON WW 16, 2001  
IN THE ASSEMBLY LINE "A"

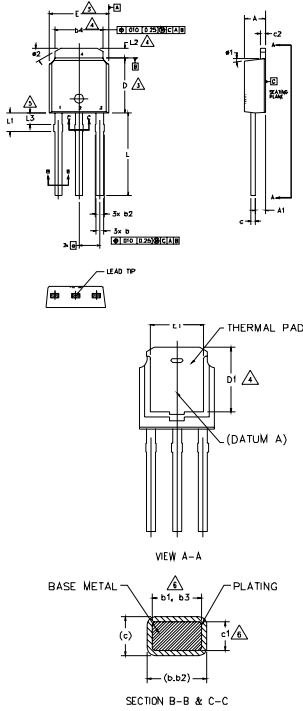
Note: "P" in assembly line position  
indicates "Lead-Free"  
"P" in assembly line position indicates  
"Lead-Free" qualification to the Consumer-level

OR



## I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



**NOTES:**

- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- 2.- DIMENSION ARE SHOWN IN INCHES [MILLIMETERS]
- △ DIMENSION B & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
- △- THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
- △- LEAD DIMENSION UNCONTROLLED IN L3.
- △- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
- 7.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA (Date 06/02).
- 8.- CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	0.89	1.14	.035	.045	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	6
b2	0.76	1.14	.030	.045	
b3	0.76	1.04	.030	.041	6
b4	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	6
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	3
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	3
E1	4.32	-	.170	-	4
e	2.29 BSC	-	.090 BSC	-	
L	8.89	9.65	.350	.380	
L1	1.91	2.29	.075	.090	
L2	0.89	1.27	.035	.050	4
L3	1.14	1.52	.045	.060	5
ø1	0"	15"	0"	15"	
ø2	25"	35"	25"	35"	

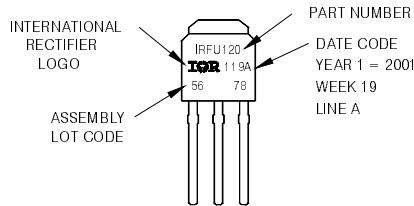
LEAD ASSIGNMENTS

- HEXFET
- 1.- GATE
  - 2.- DRAIN
  - 3.- SOURCE
  - 4.- DRAIN

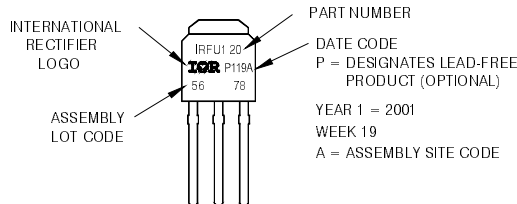
## I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120  
WITH ASSEMBLY  
LOT CODE 5678  
ASSEMBLED ON WW 19, 2001  
IN THE ASSEMBLY LINE 'A'

Note: 'P' in assembly line position  
indicates Lead-Free'



OR

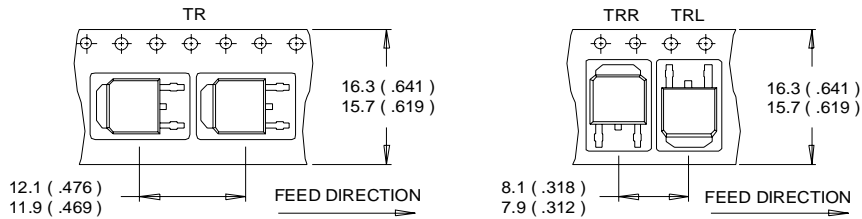


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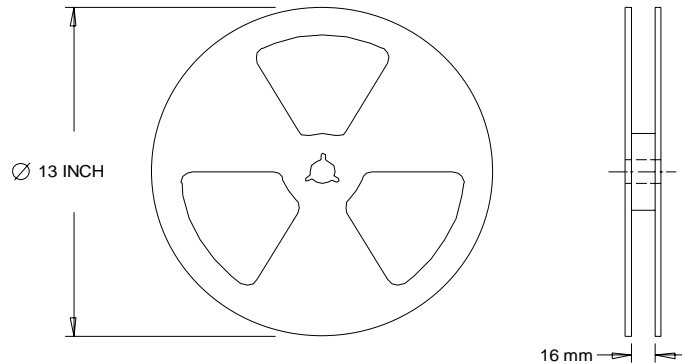
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**IR** Rectifier

## D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS ( INCHES ).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. OUTLINE CONFORMS TO EIA-481.

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.54\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 28\text{A}$ .
- ③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 30A.
- ⑤  $R_\theta$  is measured at  $T_J$  approximately  $90^\circ\text{C}$

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Consumer market.  
Qualification Standards can be found on IR's Web site.

International  
**IR** Rectifier

**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
TAC Fax: (310) 252-7903

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[www.irf.com](http://www.irf.com)

Note: For the most current drawings please refer to the IR website at:  
<http://www.irf.com/package/>

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-  Cost Control Management
-  Shortage Management
-  Alternative Solution
-  Excess Inventory Management